MC74VHC595

8-Bit Shift Register with Output Storage Register
(3-State)

The MC74VHC595 is an advanced high speed 8−bit shift register with an output storage register fabricated with silicon gate CMOS technology.

It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The MC74VHC595 contains an 8−bit static shift register which feeds an 8−bit storage register.

Shift operation is accomplished on the positive going transition of the Shift Clock input (SCK). The output register is loaded with the contents of the shift register on the positive going transition of the Register Clock input (RCK). Since the RCK and SCK signals are independent, parallel outputs can be held stable during the shift operation. And, since the parallel outputs are 3−state, the VHC595 can be directly connected to an 8−bit bus. This register can be used in serial−to−parallel conversion, data receivers, etc.

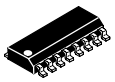
The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7V, allowing the interface of 5V systems to 3V systems.

- High Speed: f_{max} = 185MHz (Typ) at V_{CC} = 5V
- Low Power Dissipation: I_{CC} = 4μA (Max) at T_A = 25°C
- High Noise Immunity: $V_{NIH} = V_{NIL}$ = 28% V_{CC}
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2V to 5.5V Operating Range
- Low Noise: V_{OLP} = 1.0V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300mA
- ESD Performance: HBM > 2000V; Machine Model > 200V
- **These devices are available in Pb−free package(s). Specifications herein apply to both standard and Pb−free devices. Please see our website at www.onsemi.com for specific Pb−free orderable part numbers, or contact your local ON Semiconductor sales office or representative.**

ON Semiconductor®

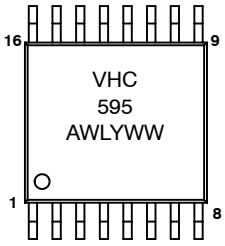
http://onsemi.com

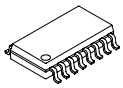
MARKING DIAGRAMS



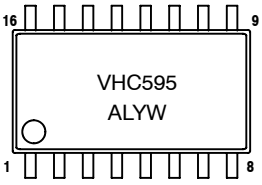
SOIC−16
D SUFFIX
CASE 751B

TSSOP−16
DT SUFFIX
CASE 948F





SOIC EIAJ−16
M SUFFIX
CASE 966



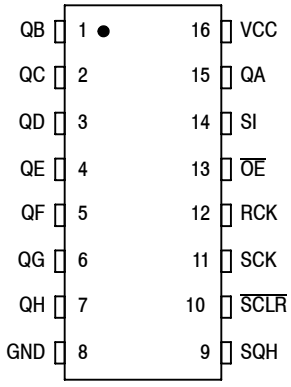
A = Assembly Location
WL = Wafer Lot
YY = Year
WW = Work Week

A = Assembly Location	A = Assembly Location
WL = Wafer Lot	L = Wafer Lot
Y = Year	Y = Year
WW = Work Week	W = Work Week

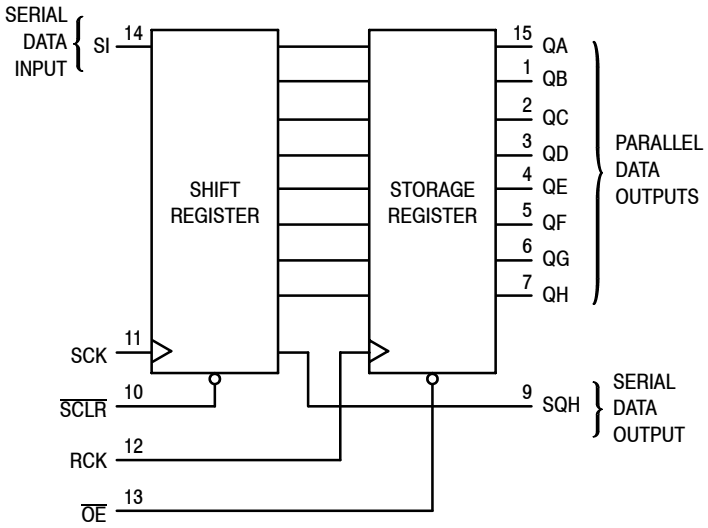
ORDERING INFORMATION

Device	Package	Shipping
MC74VHC595D	SOIC−16	48 Units/Rail
MC74VHC595DR2	SOIC−16	2500 Units/Reel
MC74VHC595DT	TSSOP−16	96 Units/Rail
MC74VHC595DTEL	TSSOP−16	2000 Units/Reel
MC74VHC595DTR2	TSSOP−16	2500 Units/Reel
MC74VHC595M	SOIC EIAJ−16	50 Units/Rail
MC74VHC595MEL	SOIC EIAJ−16	2000 Units/Reel

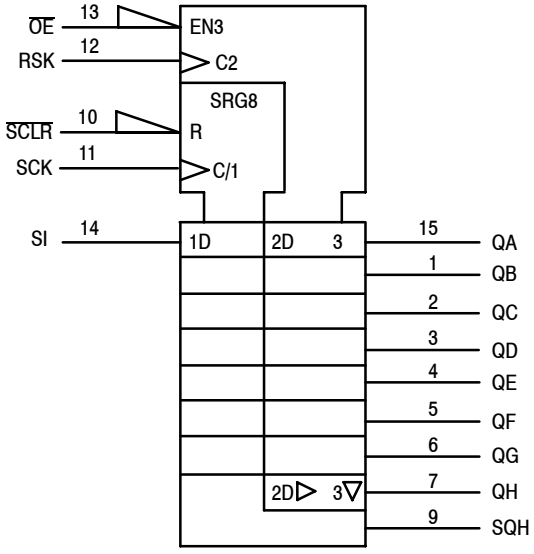
PIN ASSIGNMENT



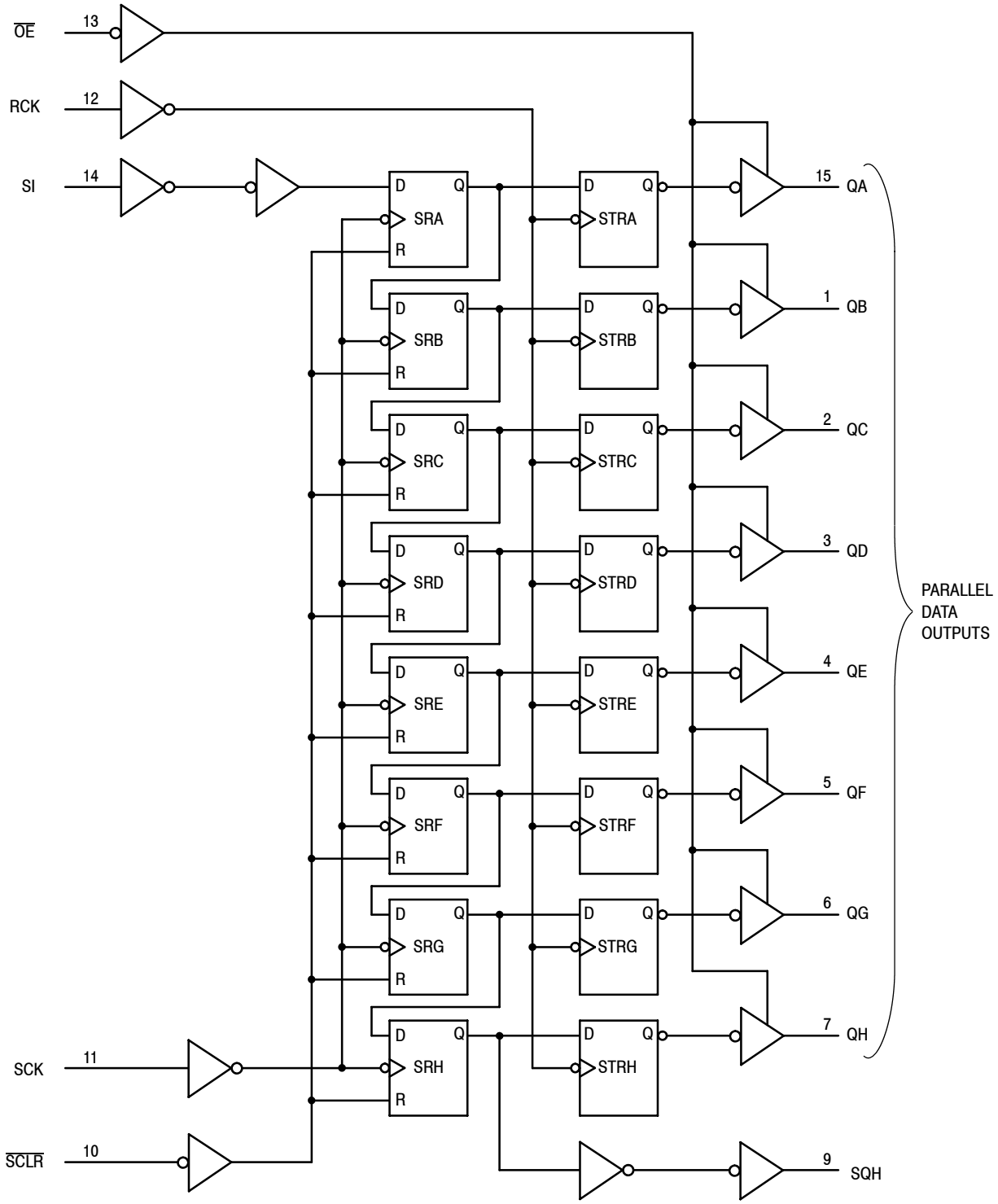
LOGIC DIAGRAM



IEC LOGIC SYMBOL



EXPANDED LOGIC DIAGRAM



FUNCTION TABLE

Operation	Inputs					Resulting Function			
	Reset ($\overline{SCLR}$)	Serial Input (SI)	Shift Clock (SCK)	Reg Clock (RCK)	Output Enable ($\overline{OE}$)	Shift Register Contents	Storage Register Contents	Serial Output (SQH)	Parallel Outputs (QA - QH)
Clear shift register	L	X	X	L, H, ↓	L	L	U	L	U
Shift data into shift register	H	D	↑	L, H, ↓	L	D→SR_A; SR_N→SR_{N+1}	U	SR_G→SR_H	U
Registers remains unchanged	H	X	L, H, ↓	X	L	U	**	U	**
Transfer shift register contents to storage register	H	X	L, H, ↓	↑	L	U	SR_N→STR_N	*	SR_N
Storage register remains unchanged	X	X	X	L, H, ↓	L	*	U	*	U
Enable parallel outputs	X	X	X	X	L	*	**	*	Enabled
Force outputs into high impedance state	X	X	X	X	H	*	**	*	Z

SR = shift register contents D = data (L, H) logic level ↓ = High-to-Low * = depends on Reset and Shift Clock inputs
STR = storage register contents U = remains unchanged ↑ = Low-to-High ** = depends on Register Clock input

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage	− 0.5 to + 7.0	V
V_{in}	DC Input Voltage	− 0.5 to + 7.0	V
V_{out}	DC Output Voltage	− 0.5 to V_{CC} + 0.5	V
I_{IK}	Input Diode Current	- 20	mA
I_{OK}	Output Diode Current	± 20	mA
I_{out}	DC Output Current, per Pin	± 25	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	± 50	mA
P_D	Power Dissipation in Still Air, SOIC Packages† TSSOP Package†	500 450	mW
T_{stg}	Storage Temperature	− 65 to + 150	°C

* Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied.

†Derating — SOIC Packages: − 7 mW/°C from 65° to 125°C
TSSOP Package: - 6.1 mW/°C from 65° to 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND ≤ (V_{in} or V_{out}) ≤ V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	DC Supply Voltage		2.0	5.5	V
V_{in}	DC Input Voltage		0	5.5	V
V_{out}	DC Output Voltage		0	V_{CC}	V
T_A	Operating Temperature, All Package Types		- 55	+ 125	°C
t_r, t_f	Input Rise and Fall Time	V_{CC} = 3.3V ±0.3V V_{CC} =5.0V ±0.5V	0 0	100 20	ns/V

The θ_{JA} of the package is equal to 1/Derating. Higher junction temperatures may affect the expected lifetime of the device per the table and figure below.

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

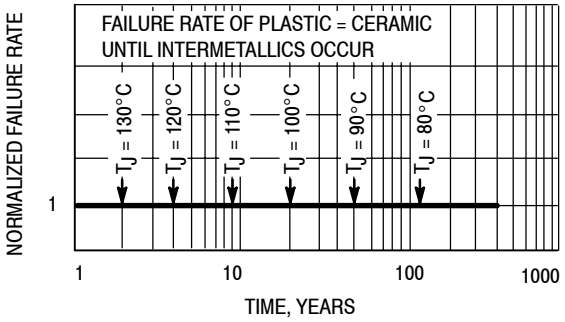


Figure 1. Failure Rate vs. Time Junction Temperature

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V_{CC} (V)	T_A = 25°C			T_A = ≤ 85°C		T_A = ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V_{IH}	Minimum High−Level Input Voltage		2.0 3.0 4.5 5.5	1.5 2.1 3.15 3.85			1.5 2.1 3.15 3.85		1.5 2.1 3.15 3.85		V
V_{IL}	Maximum Low−Level Input Voltage		2.0 3.0 4.5 5.5			0.59 0.9 1.35 1.65		0.59 0.9 1.35 1.65		0.59 0.9 1.35 1.65	V
V_{OH}	Minimum High−Level Output Voltage V_{IN} = V_{IH} or V_{IL}	V_{IN} = V_{IH} or V_{IL} I_{OH} = − 50 μA	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		V_{IN} = V_{IH} or V_{IL} I_{OH} = −4 mA I_{OH} = −8 mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		
V_{OL}	Maximum Low−Level Output Voltage V_{IN} = V_{IH} or V_{IL}	V_{IN} = V_{IH} or V_{IL} I_{OL} = 50 μA	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		V_{IN} = V_{IH} or V_{IL} I_{OL} = 4 mA I_{OL} = 8 mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I_{IN}	Maximum Input Leakage Current	V_{IN} = 5.5 V or GND	0 to 5.5			± 0.1		± 1.0		± 1.0	μA
I_{CC}	Maximum Quiescent Supply Current	V_{IN} = V_{CC} or GND	5.5			4.0		40.0		40.0	μA
I_{OZ}	Three−State Output Off−State Current	V_{IN} = V_{IH} or V_{IL} V_{OUT} = V_{CC} or GND	5.5			± 0.25		± 2.5		± 2.5	μA

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0$ns)

Symbol	Parameter	Test Conditions	$T_A = 25°C$ Min	$T_A = 25°C$ Typ	$T_A = 25°C$ Max	$T_A \le 85°C$ Min	$T_A \le 85°C$ Max	$T_A \le 125°C$ Min	$T_A \le 125°C$ Max	Unit
f_{max}	Maximum Clock Frequency (50% Duty Cycle)	V_{CC} = 3.3 ± 0.3 V	80	150		70		70		MHz
		V_{CC} = 5.0 ± 0.5 V	135	185		115		115		
t_{PLH}, t_{PHL}	Propagation Delay, SCK to SQH	V_{CC} = 3.3 ± 0.3 V C_L = 15pF		8.8	13.0	1.0	15.0	1.0	15.0	ns
		V_{CC} = 3.3 ± 0.3 V C_L = 50pF		11.3	16.5	1.0	18.5	1.0	18.5	
		V_{CC} = 5.0 ± 0.5 V C_L = 15pF		6.2	8.2	1.0	9.4	1.0	9.4	
		V_{CC} = 5.0 ± 0.5 V C_L = 50pF		7.7	10.2	1.0	11.4	1.0	11.4	
t_{PHL}	Propagation Delay, $\overline{CPLR}$ to SQH	V_{CC} = 3.3 ± 0.3 V C_L = 15pF		8.4	12.8	1.0	13.7	1.0	13.7	ns
		V_{CC} = 3.3 ± 0.3 V C_L = 50pF		10.9	16.3	1.0	17.2	1.0	17.2	
		V_{CC} = 5.0 ± 0.5 V C_L = 15pF		5.9	8.0	1.0	9.1	1.0	9.1	
		V_{CC} = 5.0 ± 0.5 V C_L = 50pF		7.4	10.0	1.0	11.1	1.0	11.1	
t_{PLH}, t_{PHL}	Propagation Delay, RCK to QA-QH	V_{CC} = 3.3 ± 0.3 V C_L = 15pF		7.7	11.9	1.0	13.5	1.0	13.5	ns
		V_{CC} = 3.3 ± 0.3 V C_L = 50pF		10.2	15.4	1.0	17.0	1.0	17.0	
		V_{CC} = 5.0 ± 0.5 V C_L = 15pF		5.4	7..4	1.0	8.5	1.0	8.5	
		V_{CC} = 5.0 ± 0.5 V C_L = 50pF		6.9	9.4	1.0	10.5	1.0	10.5	
t_{PZL}, t_{PZH}	Output Enable Time, $\overline{OE}$ to QA-QH	V_{CC} = 3.3 ± 0.3 V C_L = 15pF R_L = 1 kΩ		7.5	11.5	1.0	13.5	1.0	13.5	ns
		V_{CC} = 3.3 ± 0.3 V C_L = 50pF R_L = 1 kΩ		9.0	15.0	1.0	17.0	1.0	17.0	
		V_{CC} = 5.0 ± 0.5 V C_L = 15pF R_L = 1 kΩ		4.8	8.6	1.0	10.0	1.0	10.0	
		V_{CC} = 5.0 ± 0.5 V C_L = 50pF R_L = 1 kΩ		8.3	10.6	1.0	12.0	1.0	12.0	
t_{PLZ}, t_{PHZ}	Output Disable Time, $\overline{OE}$ to QA-QH	V_{CC} = 3.3 ± 0.3 V C_L = 50pF R_L = 1 kΩ		12.1	15.7	1.0	16.2	1.0	16.2	ns
		V_{CC} = 5.0 ± 0.5 V C_L = 50pF R_L = 1 kΩ		7.6	10.3	1.0	11.0	1.0	11.0	
C_{IN}	Input Capacitance			4	10		10		10	pF
C_{OUT}	Three-State Output Capacitance (Output in High-Impedance State), QA-QH			6			10		10	pF

		Typical @ 25°C, V_{CC} = 5.0V	
C_{PD}	Power Dissipation Capacitance (Note 1)	87	pF

1. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no-load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0$ns, C_L = 50pF, V_{CC} = 5.0V)

Symbol	Characteristic	$T_A = 25°C$ Typ	$T_A = 25°C$ Max	Unit
V_{OLP}	Quiet Output Maximum Dynamic V_{OL}	0.8	1.0	V
V_{OLV}	Quiet Output Minimum Dynamic V_{OL}	- 0.8	- 1.0	V
V_{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V_{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

TIMING REQUIREMENTS (Input $t_r = t_f = 3.0$ns)

Symbol	Parameter	V_{CC} V	$T_A = 25°C$ Typ	$T_A = 25°C$ Limit	T_A = - 40 to 85°C Limit	T_A = - 55 to 125°C Limit	Unit
t_{su}	Setup Time, SI to SCK	3.3		3.5	3.5	3.5	ns
		5.0		3.0	3.0	3.0	
$t_{su(H)}$	Setup Time, SCK to RCK	3.3		8.0	8.5	8.5	ns
		5.0		5.0	5.0	5.0	

TIMING REQUIREMENTS (Input $t_r = t_f = 3.0$ns)

Symbol	Parameter	V_{CC} V	Typ	Limit	Limit	Limit	Unit
$t_{su(L)}$	Setup Time, $\overline{SCLR}$ to RCK	3.3 5.0		8.0 5.0	9.0 5.0	9.0 5.0	ns
t_h	Hold Time, SI to SCK	3.3 5.0		1.5 2.0	1.5 2.0	1.5 2.0	ns
$t_{h(L)}$	Hold Time, $\overline{SCLR}$ to RCK	3.3 5.0		0 0	0 0	1.0 1.0	ns
t_{rec}	Recovery Time, $\overline{SCLR}$ to SCK	3.3 5.0		3.0 2.5	3.0 2.5	3.0 2.5	ns
t_w	Pulse Width, SCK or RCK	3.3 5.0		5.0 5.0	5.0 5.0	5.0 5.0	ns
$t_{w(L)}$	Pulse Width, $\overline{SCLR}$	3.3 5.0		5.0 5.0	5.0 5.0	5.0 5.0	ns

SWITCHING WAVEFORMS

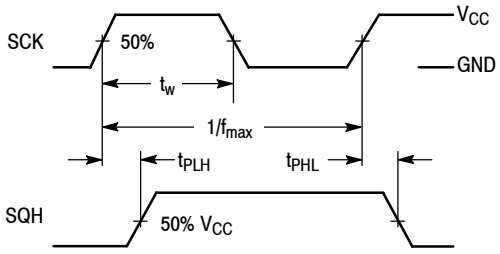


Figure 2.

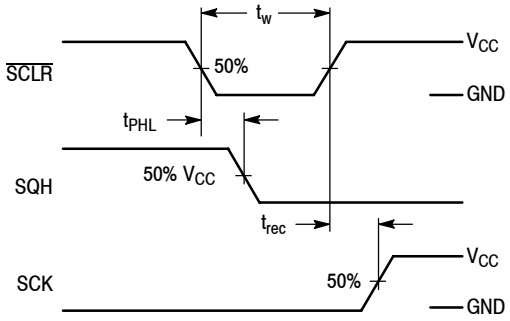


Figure 3.

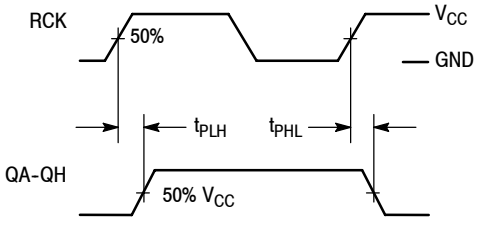


Figure 4.

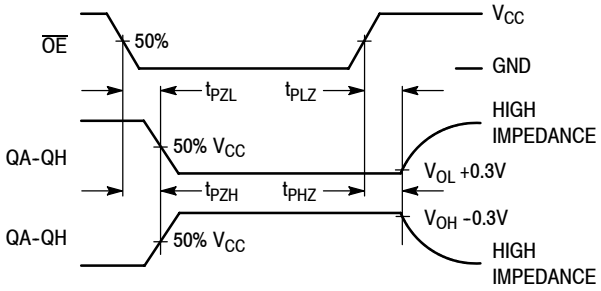


Figure 5.

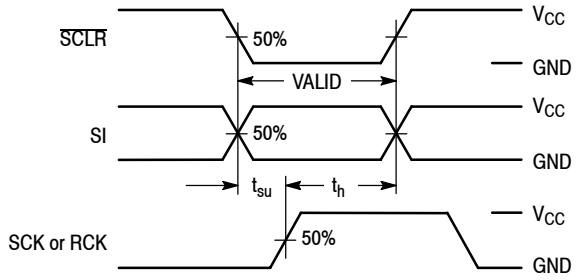


Figure 6.

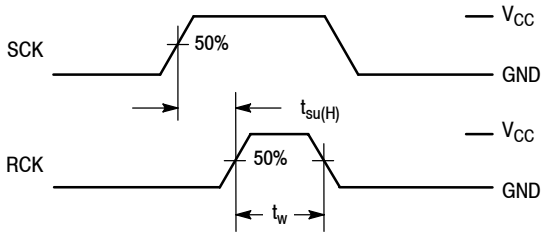
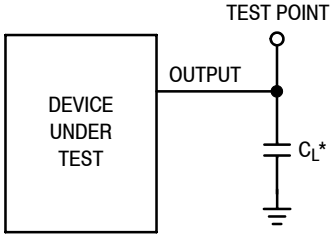


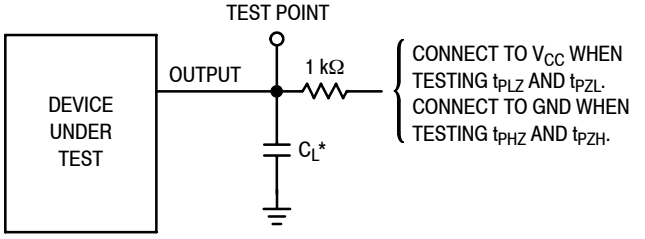
Figure 7.

TEST CIRCUITS



*Includes all probe and jig capacitance

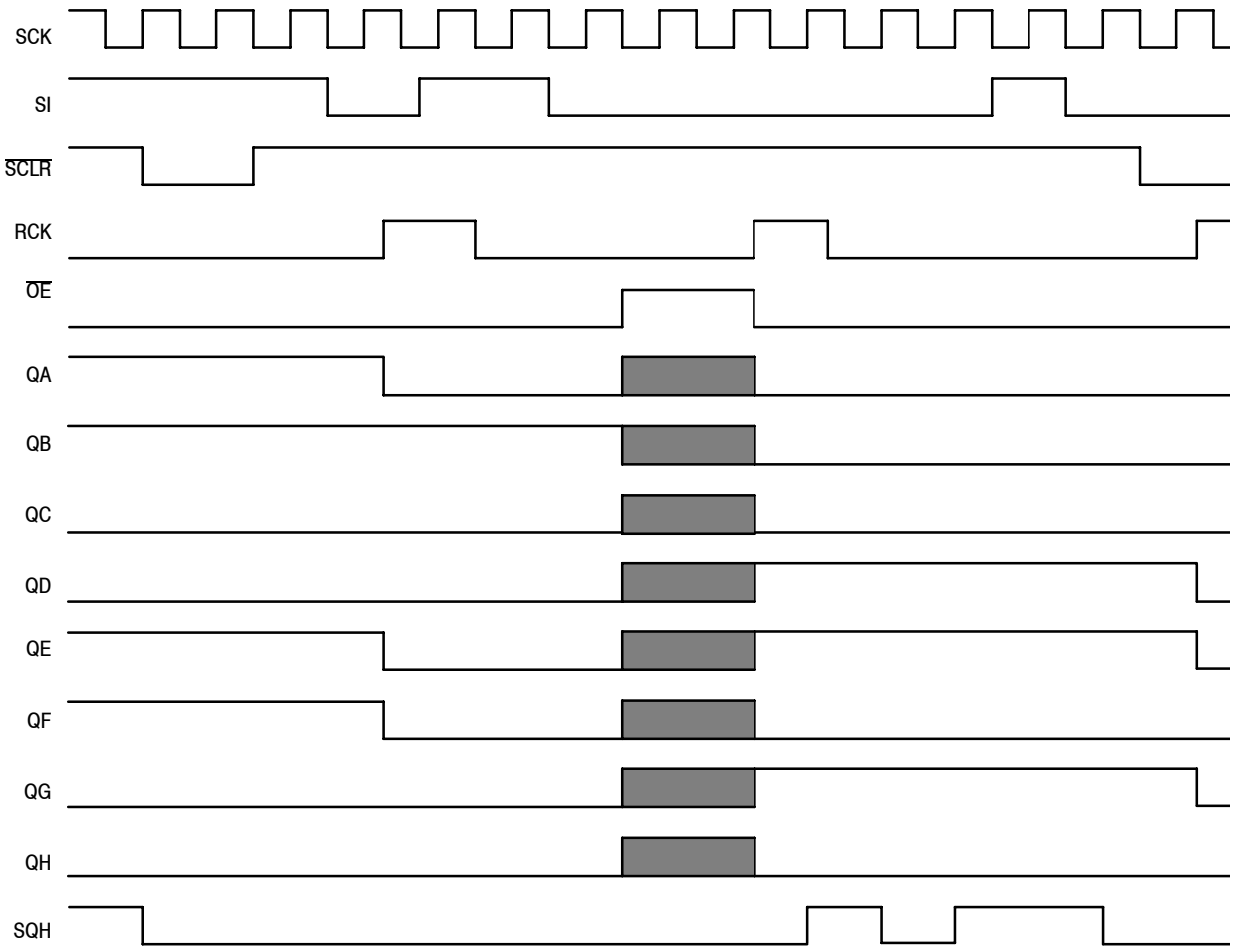
Figure 8.



*Includes all probe and jig capacitance

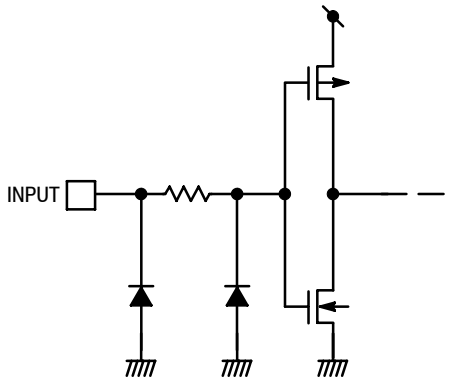
Figure 9.

TIMING DIAGRAM



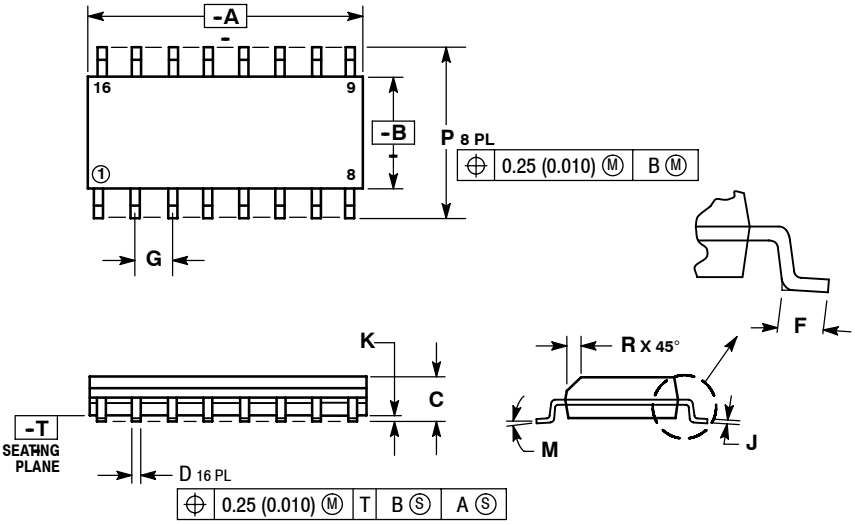
NOTE: output is in a high−impedance state.

INPUT EQUIVALENT CIRCUIT



PACKAGE DIMENSIONS

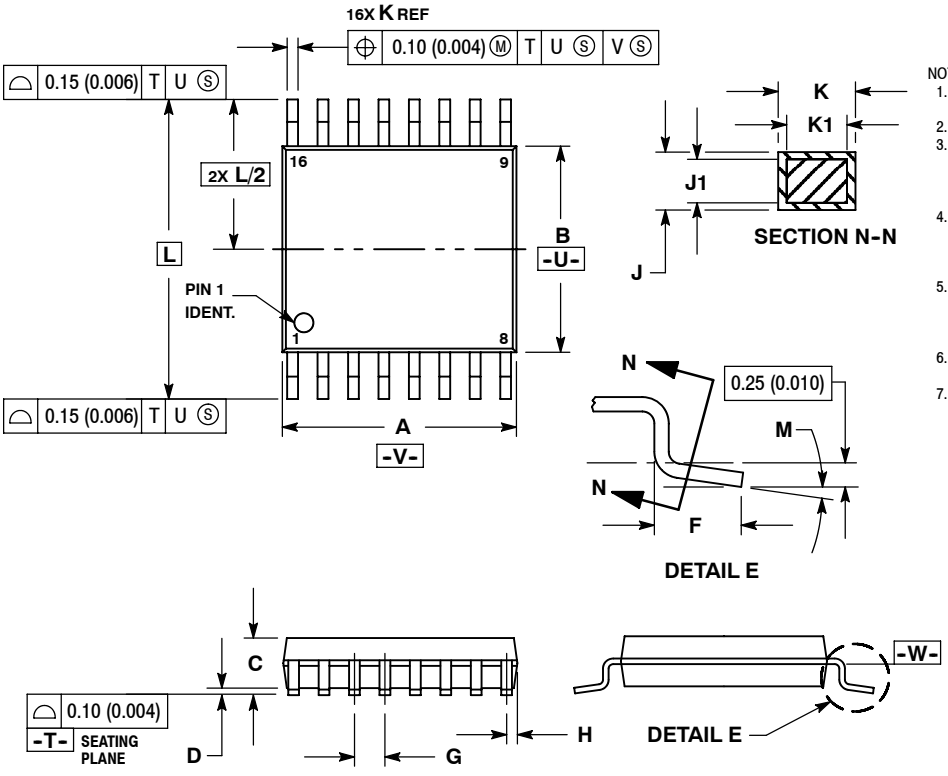
SOIC-16
D SUFFIX
CASE 751B-05
ISSUE J



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	9.80	10.00	0.386	0.393
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

TSSOP-16
DT SUFFIX
CASE 948F-01
ISSUE O

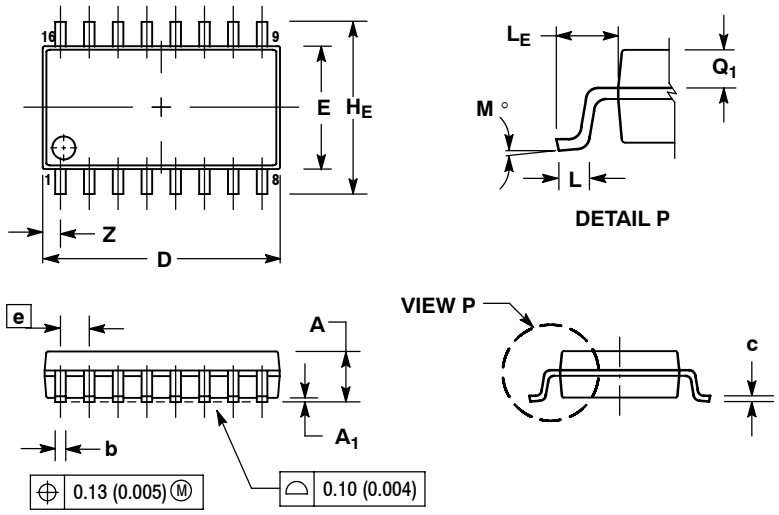


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0 °	8 °	0 °	8 °

PACKAGE DIMENSIONS

SOIC EIAJ-16
M SUFFIX
CASE 966-01
ISSUE O



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	---	2.05	---	0.081
A_1	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
H_E	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
L_E	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10 °
Q_1	0.70	0.90	0.028	0.035
Z	---	0.78	---	0.031

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082-1312 USA
Phone: 480-829-7710 or 800-344-3860 Toll Free USA/Canada
Fax: 480-829-7709 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center
2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051
Phone: 81-3-5773-3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.